

Supporting information

All Solution-Processed Hafnium Rich Hybrid Dielectrics for Hysteresis Free Metal-Oxide Thin-film Transistors

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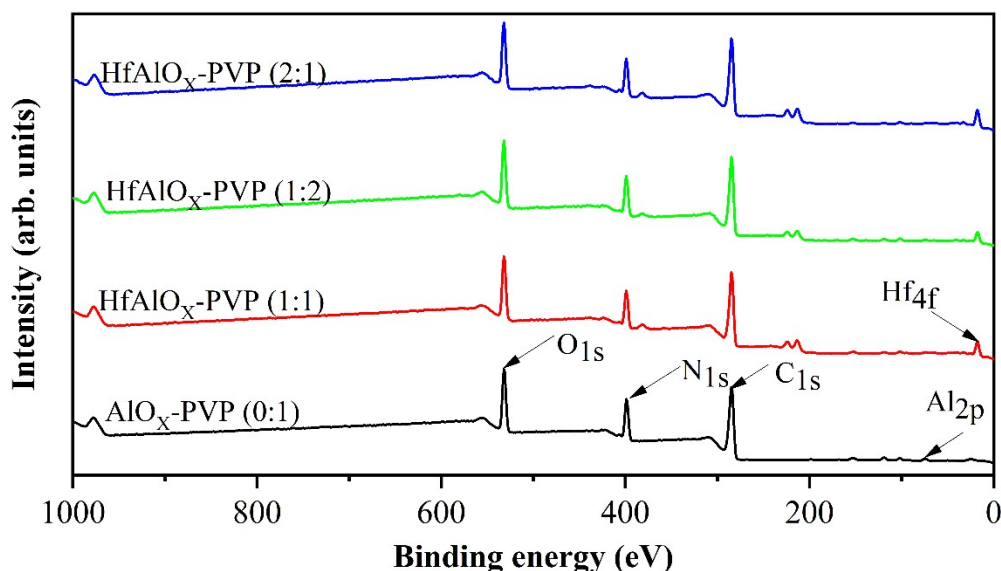


Fig.S1. XPS survey scan spectra of AlO_x-PVP and HfAlO_x-PVP hybrid thin films.

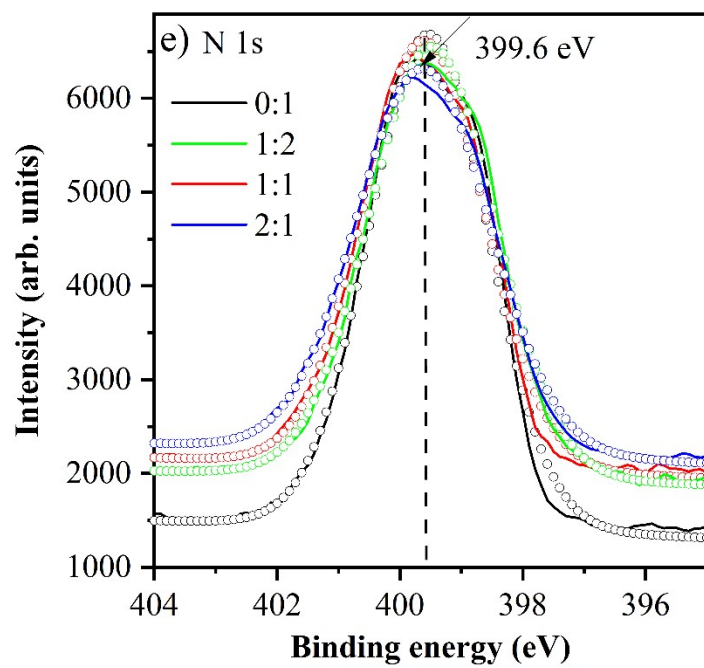


Fig.S2 XPS spectra of AlOx-PVP and HfAlOx-PVP hybrid thin films f) N 1s spectra.

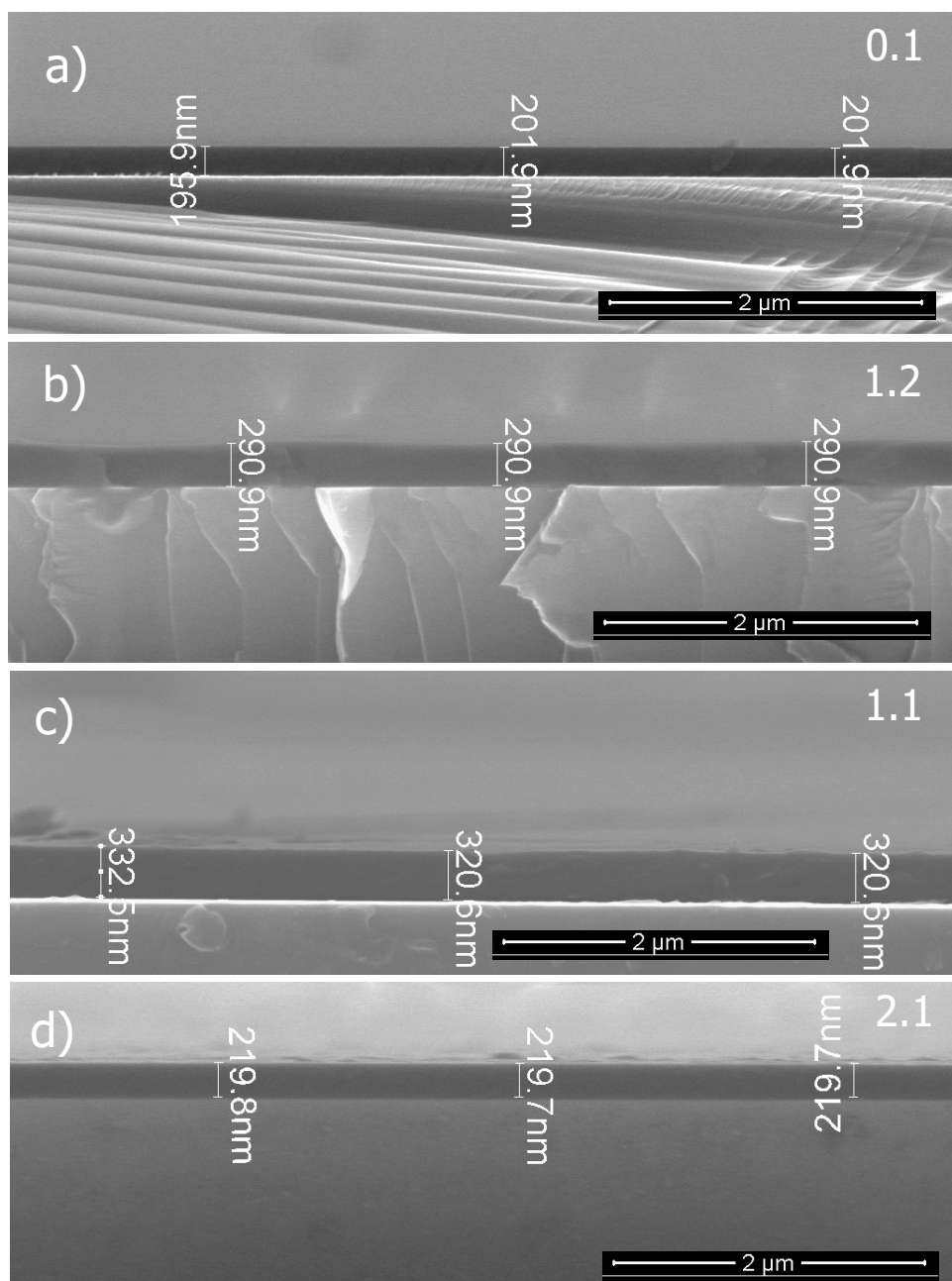
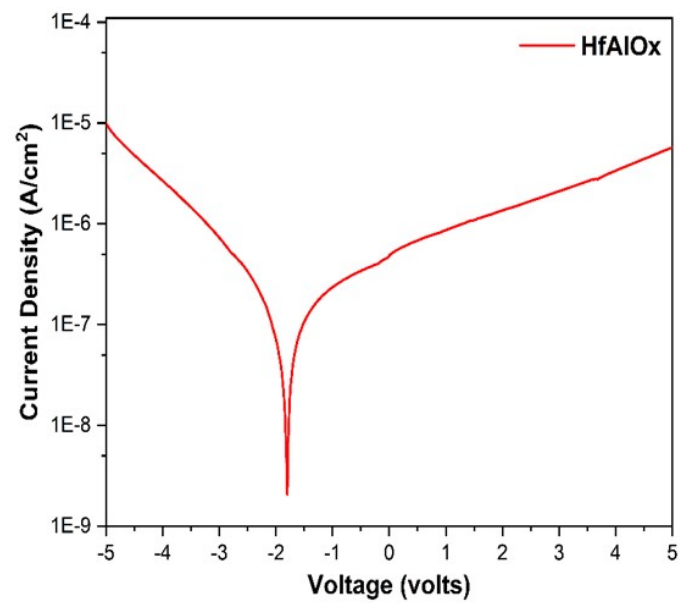


Fig.S3 FESEM cross section images of AlO_x-PVP and HfAlO_x-PVP hybrid dielectric thin films

a) 0:1 b) 1:2 c) 1:1 and d) 2:1.



FigS4. Leakage current density (I-V) plot of HfAlOx (1:1) inorganic dielectric.